

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2310	438/458.ccls. 438/459.ccls. 438/463.ccls. 438/479.ccls. 438/940.ccls. 438/977.ccls.	US-PGPUB; USPAT	OR	OFF	2005/01/19 08:23
L2	229	(438/458.ccls. 438/459.ccls. 438/463.ccls. 438/479.ccls. 438/940.ccls. 438/977.ccls.) and (gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride))	US-PGPUB; USPAT	OR	ON	2005/01/19 08:25
L3	224	(gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride)) same (laser with (separat\$6 remov\$6 ablat\$6)) same ((growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	US-PGPUB; USPAT	OR	ON	2005/01/19 10:08
L4	55	(gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride)) and (laser with (separat\$6 remov\$6 ablat\$6)) and ((growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 09:58
L5	127	1 and (laser with (separat\$6 remov\$6 ablat\$6)) and ((growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	US-PGPUB; USPAT	OR	ON	2005/01/19 10:10
L6	947	1 and ((laser with (separat\$6 remov\$6 ablat\$6)) (growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	US-PGPUB; USPAT	OR	ON	2005/01/19 10:11